

L Number	Hits	Search Text	DB	Time stamp
1	1885	((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.	USPAT; US-PGPUB	2003/04/06 17:41
2	99764	irradiate or irradiation	USPAT; US-PGPUB	2003/04/06 17:45
3	595	((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation))	USPAT; US-PGPUB	2003/04/06 17:46
4	1217179	metal	USPAT; US-PGPUB	2003/04/06 17:46
5	497	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal	USPAT; US-PGPUB	2003/04/06 17:46
6	622038	channel	USPAT; US-PGPUB	2003/04/06 17:46
7	458	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel	USPAT; US-PGPUB	2003/04/06 17:48
8	325606	semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
9	451	(((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor	USPAT; US-PGPUB	2003/04/06 17:48
10	661709	protrusion or project or projection	USPAT; US-PGPUB	2003/04/06 17:50
11	141	((((((438/149) or (438/151) or (438/161) or (438/164) or (438/166)).CCLS.) and (irradiate or irradiation)) and metal) and channel) and semiconductor) and (protrusion or project or projection)	USPAT; US-PGPUB	2003/04/06 17:50
-	0	(heat adj absorb\$3) with insulat\$3 with ((non-single or poly or polycrystalline) adj (film or layer)) with recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 11:43
-	2	(heat adj absorb\$3) and insulat\$3 and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 11:47
-	6766	(heat adj absorb\$3) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:01
-	2	((heat adj absorb\$3) and insulat\$3) and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 11:48
-	0	((heat adj absorb\$3) with metal) and insulat\$3 and amorphous and ((non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:04
-	0	((heat adj absorb\$3) with metal) and insulat\$3 and ((amorphous or non-single or poly or polycrystalline) adj (film or layer)) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:05
-	1320	(heat adj absorb\$3) with metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 12:15

-	499	((heat adj absorb\$3) with metal) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:06
-	4	((((heat adj absorb\$3) with metal) and insulat\$3) and (non-single or poly or polycrystalline) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:08
-	24	((((heat adj absorb\$3) with metal) and insulat\$3) and (non-single or poly or polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:08
-	1888852	((heat adj absorb\$3 or metal) adj layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:08
-	13	(heat adj absorb\$3 with metal) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:19
-	538	(heat adj absorb\$3) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:39
-	1	((((heat adj absorb\$3) adj (layer or film)) same metal) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:21
-	0	((((heat adj absorb\$3) adj (layer or film)) same metal) and recrystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:21
-	105	((heat adj absorb\$3) adj (layer or film)) same metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:22
-	1	((heat adj absorb\$3) adj (layer or film)) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 12:39
-	20154	((heat adj absorb\$3 or metal) adj layer or film) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:18
-	3477	((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:19
-	2873	((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:20
-	0	(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and irradat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 15:21

-	1208	(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:22
-	628	(((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:22
-	615	((((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 15:23
-	35	(((((((heat adj absorb\$3 or metal) adj layer or film) and tft) and polycrystalline) and insulat\$3) and crystalliz\$5) and island\$1) and semiconductor) and protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:12
-	0	irradiat\$4 with protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:14
-	400	irradiat\$4 with protrusion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:23
-	1	(irradiat\$4 with protrusion\$1) with tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:16
-	0	((irradiat\$4 with protrusion\$1) with tft) with crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:17
-	0	((irradiat\$4 with protrusion\$1) with tft) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:17
-	24	irradiat\$4 with (protrusion\$1 same semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:23
-	220	irradiat\$4 and (protrusion\$1 same semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 17:24
-	0	metal with insulat\$3 with amorphous with irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:06
-	21	metal and insulat\$3 and amorphous and irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:07
-	121266	metal adj(layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/14 18:08

-	121266	metal adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
-	3067	((metal adj (layer or film)) and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
-	2727	((metal adj (layer or film)) and tft) and insulat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:09
-	613	((((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:11
-	368	((((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:13
-	53	(((((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4) and (semiconductor adj island)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:13
-	53	(((((metal adj (layer or film)) and tft) and insulat\$4) and crystalliz\$5) and irradiat\$4) and (semiconductor adj island) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/14 18:14
-	0	tft with island\$1 with amorphous with crystalliz\$5 with irradat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:35
-	0	tft and island\$1 with amorphous near5 crystalliz\$5 with irradat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:35
-	0	tft and island\$1 and amorphous near5 crystalliz\$5 with irradat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:36
-	1	tft with island\$1 with amorphous near5 crystalliz\$5 with irradiat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 10:36
-	0	20010045558.URPN.	USPAT	2002/08/15 15:29
-	0	20010045558.URPN.	USPAT	2002/08/15 15:29
-	2	protrusion\$1 with crystalliz\$5 adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:08
-	1	(rough\$4 with recrystalliz\$5) with hsg	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 19:09
-	0	20020036312.URPN.	USPAT	2002/08/15 19:10

-	711	rough\$4 same recrystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/08/15 19:12
-	292	rough\$4 with recrystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/08/15 19:46
-	8	(rough\$4 with recrystalliz\$5) with amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/08/15 19:14
-	0	20020034845.URPN.	USPAT	2002/08/15 19:18
-	15	("4411734" "4737474" "5089432" "5121186" "5147820" "5147826" "5298436" "5326722" "5418398" "5441904" "5514621" "5604157" "5614428" "5652156" "5712181").PN.	USPAT	2002/08/15 19:23
-	2	6017819.URPN.	USPAT	2002/08/15 19:39
-	0	20020036312.URPN.	USPAT	2002/08/15 19:45
-	5	(rough\$4 with recrystalliz\$5) with semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/15 19:47